DATA SHEET

SILICON TRANSISTORS 2SC3622, 3622A

NPN SILICON EPITAXIAL TRANSISTOR FOR LOW-FREQUENCY POWER AMPLIFIERS AND SWITCHING

FEATURES

NEC

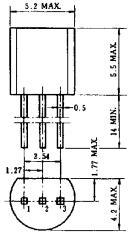
- High hFE: hFE = 1000 to 3200 @VCE = 5.0 V, IC = 1.0 mA
- Low V_{CE(sat}): V_{CE(sat}) = 0.07 V TYP. @Ic/I_B = 50 mA/5.0 mA
- High VEBO: VEBO: 12 V (2SC3622) VEBO: 15 V (2SC3622A)

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Ratings		Unit
Parameter		2SC3622	2SC3622A	Unit
Collector to base voltage	Vсво	60		V
Collector to emitter voltage	VCEO	50		V
Emitter to base voltage	VEBO	12	15	V
Collector current (DC)	IC(DC)	150		mA
Total power dissipation	P⊤	250		mW
Junction temperature	Tj	150		°C
Storage temperature	Tstg	–55 to +150		°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

PACKAGE DRAWING (UNIT: mm)



Electrode Connection					
1. Emitter	EIAJ : SC-43B				
2. Collector	JEDEC: TO-92				
3 Base	IEC : PA33				

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	$V_{CB} = 50 \text{ V}, \text{ I}_{E} = 0$			100	nA
Emitter cutoff current	Іево	V _{EB} = 10 V, Ic = 0			100	nA
DC current gain	hfe1 *	Vce = 5.0 V, Ic = 1.0 mA	1000	1800	3200	-
DC current gain	hfe2 *	Vce = 5.0 V, Ic = 100 mA	200	350		
DC base voltage	VBE *	Vce = 5.0 V, lc = 1.0 mA		560		mV
Collector saturation voltage	VCE(sat) *	Ic = 50 mA, I _B = 5.0 mA		0.07	0.30	V
Base saturation voltage	VBE(sat) *	Ic = 50 mA, I _B = 5.0 mA		0.8	1.2	V
Gain bandwidth product	f⊤	$V_{CE} = 5.0 \text{ V}, \text{ I}_{E} = -10 \text{ mA}$		250		MHz
Output capacitance	Cob	Vcb = 5 V, IE = 0, f = 1.0 MHz		3.0		pF
Turn-on time	ton	$V_{CC} = 10 \text{ V}, \text{ V}_{BE(off)} = -2.7 \text{ V}$		0.13		μs
Storage temperature	tstg	Ic = 50 mA		0.72		μs
Fall time	toff	$I_{B1} = -I_{B2} = 1 \text{ mA}$		1.22		μs

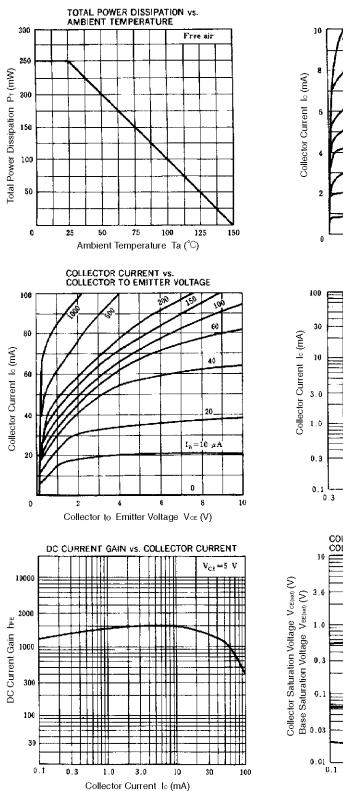
* Pulse test PW \leq 350 μ s, duty cycle \leq 2% per pulsed

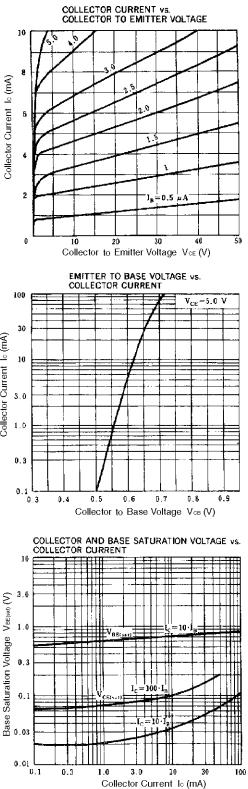
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hfe CLASSIFICATION

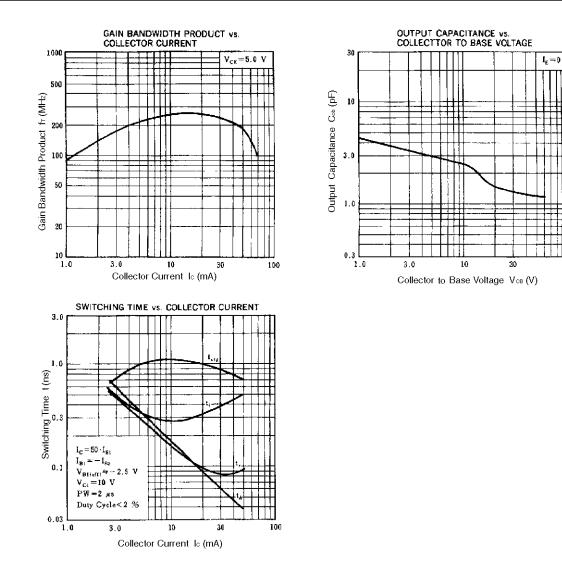
Marking	L	К
hfe1	1000 to 2000	1600 to 3200

TYPICAL CHARACTERISTICS (Ta = 25°C)





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[MEMO]

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